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ΡΛΝ	JIT
	SEMI
	CONDUCTOR

## 60V P-Channel Enhancement Mode MOSFET

Voltage

Current -15 A

### Features

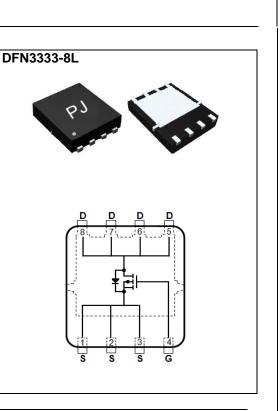
•  $R_{DS(ON)}$ ,  $V_{GS}$ @-10V,  $I_D$ @-5A<48m $\Omega$ 

-60 V

- R<sub>DS(ON)</sub>, V<sub>GS</sub>@-4.5V, I<sub>D</sub>@-3A<65mΩ
- High switching speed
- Low gate charge
- Low reverse transfer capacitance
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 Standard

### **Mechanical Data**

- Case : DFN3333-8L Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 0.001 ounces, 0.03 grams



## **Maximum Ratings and Thermal Characteristics** (T<sub>A</sub>=25<sup>o</sup>C unless otherwise noted)

PARAMETE	R	SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V <sub>DS</sub>	-60		
Gate-Source Voltage		V <sub>GS</sub>	<u>+</u> 20	- V	
Continuous Drain Current <sup>(Note 4)</sup>	T <sub>C</sub> =25°C		-15	A	
	Tc=100°C	ID	-10		
Pulsed Drain Current <sup>(Note 1)</sup>	T <sub>C</sub> =25°C	I <sub>DM</sub>	-60		
Power Dissipation	Tc=25°C	_	20	W	
	T <sub>C</sub> =100°C	PD	8		
Continuous Drain Current <sup>(Note 4)</sup>	T <sub>A</sub> =25°C		-5	А	
	T <sub>A</sub> =70°C	lo	-4		
Power Dissipation	T <sub>A</sub> =25°C	_	2	W	
	T <sub>A</sub> =70°C	PD	1.3		
Single Pulse Avalanche Energy <sup>(Note 6)</sup>		E <sub>AS</sub>	51	mJ	
Operating Junction and Storage Temperature Range		TJ,TSTG	-55~150	°C	
Typical Thermal Resistance <sup>(Note 4,5)</sup>	Junction to Case	R <sub>ejc</sub>	6.3		
	Junction to Ambient	R <sub>0JA</sub>	62.5	°C/W	



### Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

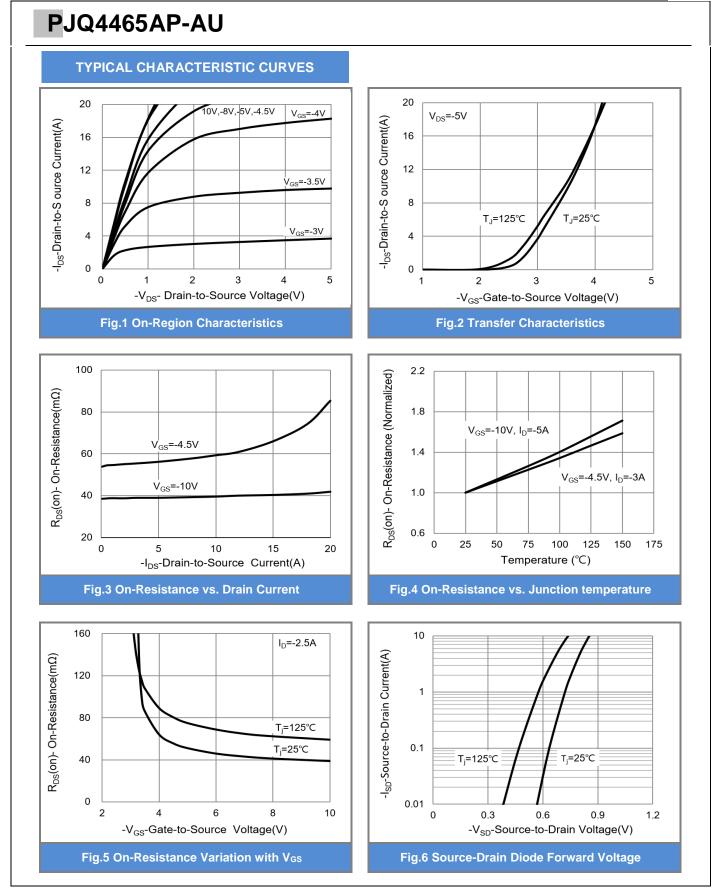
PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =-250uA	-60	-	-	
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250uA	-1	-1.7	-2.5	V
Drain-Source On-State Resistance	_	V <sub>GS</sub> =-10V, I <sub>D</sub> =-5A	-	40	48	mΩ
	RDS(on)	V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-3A	-	55	65	
Zero Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =-60V, V <sub>GS</sub> =0V	-	-	-1	uA
Gate-Source Leakage Current	lgss	V <sub>GS</sub> = <u>+</u> 20V, V <sub>DS</sub> =0V	-	-	<u>+</u> 100	nA
Dynamic <sup>(Note 7)</sup>		•				
Total Gate Charge	Qg	V <sub>DS</sub> =-30V, I <sub>D</sub> =-5A, V <sub>GS</sub> =-10V <sup>(Note 2,3)</sup>	-	22	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	4.1	-	
Gate-Drain Charge	Q <sub>gd</sub>		-	5.2	-	
Input Capacitance	Ciss	V <sub>DS</sub> =-30V, V <sub>GS</sub> =0V, f=1MHZ	-	1256	-	pF
Output Capacitance	Coss		-	87	-	
Reverse Transfer Capacitance	Crss		-	59	-	
Turn-On Delay Time	td <sub>(on)</sub>	V <sub>DD</sub> =-30V, I <sub>D</sub> =-1A, V <sub>GS</sub> =-10V, R <sub>G</sub> =6Ω (Note 2,3)	-	13	-	
Turn-On Rise Time	tr		-	42	-	
Turn-Off Delay Time	td <sub>(off)</sub>		-	65	-	ns
Turn-Off Fall Time	t <sub>f</sub>		-	16	-	
Drain-Source Diode						
Maximum Continuous Drain-Source Diode Forward Current	Is		-	-	-15	A
Diode Forward Voltage	V <sub>SD</sub>	Is=-1A, V <sub>GS</sub> =0V	-	-0.7	-1	V

NOTES :

- 1. Pulse width
- 2. Essentially independent of operating temperature typical characteristics.
- Repetitive rating, pulse width limited by junction temperature T<sub>J(MAX)</sub>=150°C. Ratings are based on low frequency and duty cycles to keep initial T<sub>J</sub> =25°C.
- 4. The maximum current rating is package limited.
- 5.  $R_{\Theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch<sup>2</sup> with 2oz.square pad of copper.
- $6. \quad L{=}0.1mH, \ I_{AS}{=}{-}32A, \ V_{GS}{=}{-}10V, \ V_{DS}{=}{-}25V, \ R_{G}{=}25 \ ohm.$
- 7. Guaranteed by design, not subject to production testing.

January 27,2022

PJQ4465AP-AU-REV.02

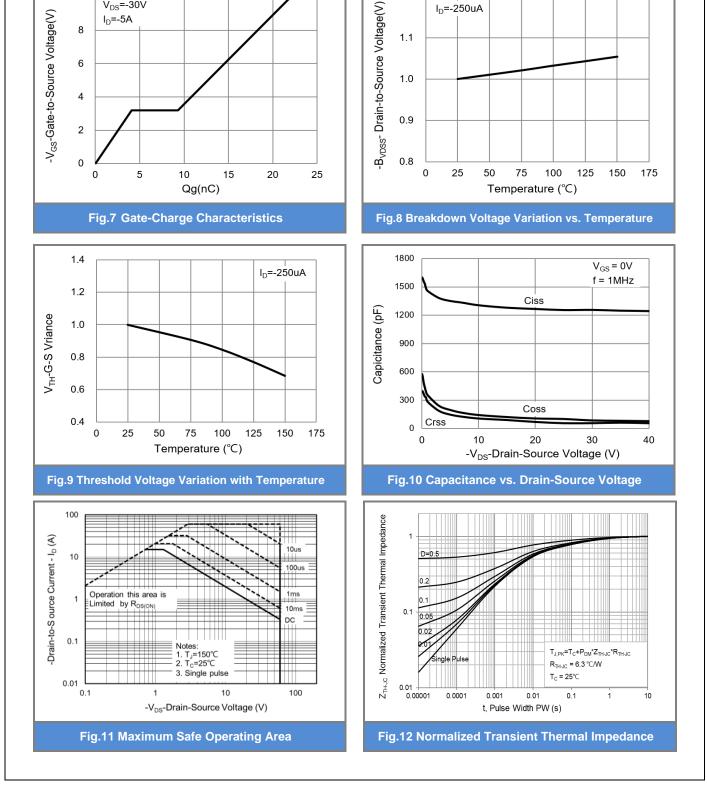




January 27,2022

#### PJQ4465AP-AU-REV.02





1.2

I<sub>D</sub>=-250uA

## **TYPICAL CHARACTERISTIC CURVES**

PJQ4465AP-AU

V<sub>DS</sub>=-30V

 $I_D = -5A$ 

PANJ SEM CONDUCTOR

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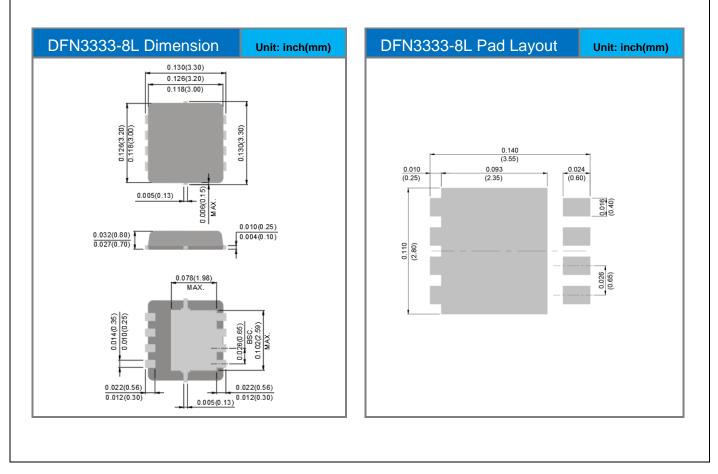




### Part No. Packing Code Version

Part No. Packing Code	Package Type	Packing Type	Marking	Version
PJQ4465AP-AU_R2_000A1	DFN3333-8L	5K pcs / 13" reel	4465	Halogen free RoHS compliant

## Packaging Information & Mounting Pad Layout





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